2SA984, 984K

2003A

PNP/NPN Epitaxial Planar Silicon Transistors

2SC2274, 2274K

Low Frequency Power Amp Applications

©465F

Features

- High breakdown voltage ($V_{CEO} \geqq 50/80V$).
- High current (I_C=500mA).
- Low saturation voltage.

( ): 2SA984,984K

Absolute Maximum Ratings at Ta=25°C

		A984,C2274	A984K,C2274K	unit
Collector to Base Voltage	V_{CBO}	(-)60	(-)100	V
Collector to Emitter Voltage	V_{CEO}	(-)50	(-)80	V
Emitter to Base Voltage	V_{EBO}	(-)5		V
Collector Current	I_C	(-)500		mA
	i_{cp}	(-)800		mA
Collector Dissipation	P_C	600		mW
Junction Temperature	Tj	150		°C
Storage Temperature	Tstg	-55 to +150		°C

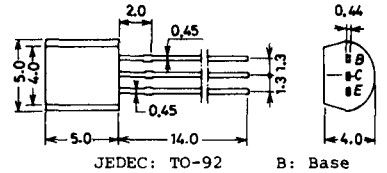
Electrical characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	V_{CB}=(-)40V, I_E=0			(-)1.0	uA
Emitter Cutoff Current	I_{EBO}	V_{EB}=(-)4V, I_C=0			(-)1.0	uA
DC Current Gain	$h_{FE}(1)$	V_{CE}=(-)5V, I_C=(-)50mA	60*		320*	
	$h_{FE}(2)$	V_{CE}=(-)5V, I_C=(-)400mA, pulse	35			
G-B Product	f_T	V_{CE}=(-)10V, I_C=(-)10mA		120		MHz
Output Capacitance	C_{ob}	V_{CB}=(-)10V, f=1MHz		(9)		pF
				5		pF
C-E Saturation Voltage	$V_{CE(sat)}$	I_C=(-)400mA, I_B=(-)40mA		(-0.25)	(-0.6)	V
				0.2	0.6	V
B-E Saturation Voltage	$V_{BE(sat)}$	" "		(-)0.9	(-)1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	I_C=(-)10uA, I_E=0 — A984,C2274	(-)60			V
		A984K,C2274K	(-)100			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	I_C=(-)1mA, R_{BE}=open — A984,C2274	(-)50			V
		A984K,C2274K	(-)80			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	I_E=(-)10uA, I_C=0	(-)5			V

* The 2SA984,K, 2SC2274,K are classified by 50mA h_{FE} as follows.

60	D	120	100	E	200	160	F	320

Case Outline 2003A
(unit:mm)



JEDEC: TO-92
EIAJ : SC-43
SANYO: NP

B: Base
C: Collector
E: Emitter

For details, refer to the description of the 2SC2274, 2274K.